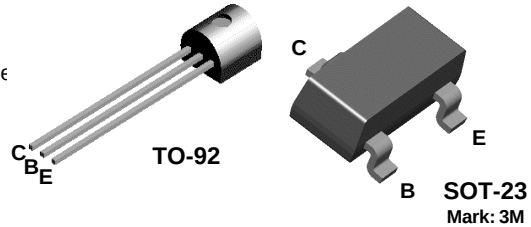


2N5210/MMBT5210

NPN General Purpose Amplifier

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1μA to 50 mA.



Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	50	V
V_{CBO}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	4.5	V
I_C	Collector Current - Continuous	100	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max.		Units
		2N5210	MMBT5210	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

NPN General Purpose Amplifier (continued)

2N5210/MMBT5210

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
--------	-----------	-----------------	-----	-----	-------

OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_B = 0$	50		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	50		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 35 \text{ V}, I_E = 0$		50	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		50	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}^*$	200 250 250	600	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.7	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$		0.85	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 500 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $f = 20 \text{ MHz}$	30		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 100 \text{ kHz}$		4.0	pF
h_{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	250	900	
NF	Noise Figure	$I_C = 20 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 22 \text{ k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$ $I_C = 20 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}$		2.0 3.0	dB dB

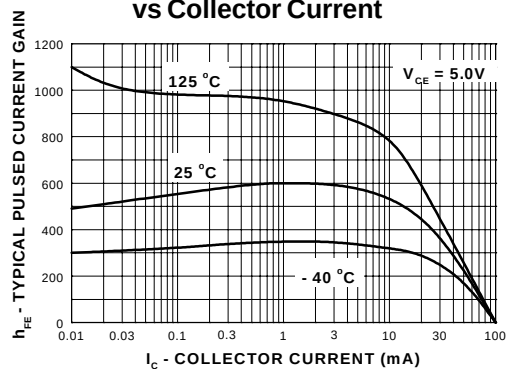
*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

NPN General Purpose Amplifier

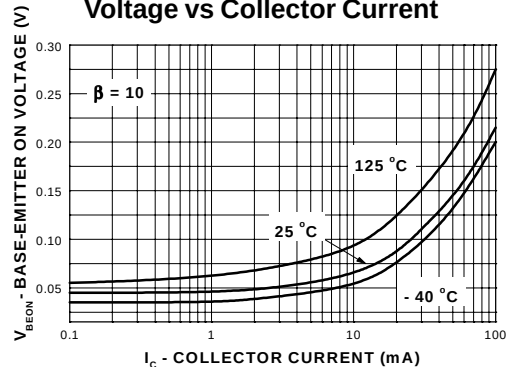
(continued)

Typical Characteristics

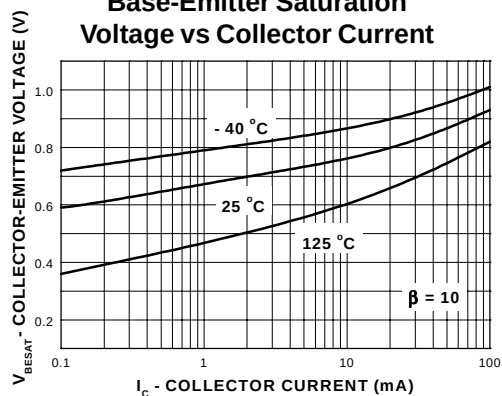
Typical Pulsed Current Gain vs Collector Current



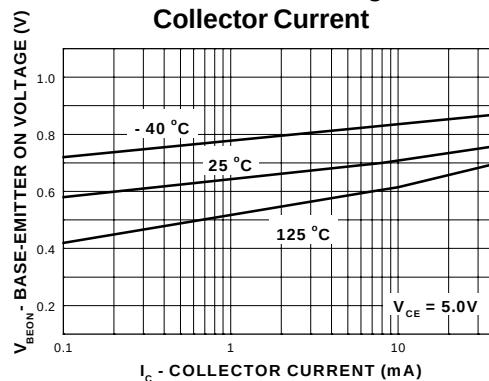
Collector-Emitter Saturation Voltage vs Collector Current



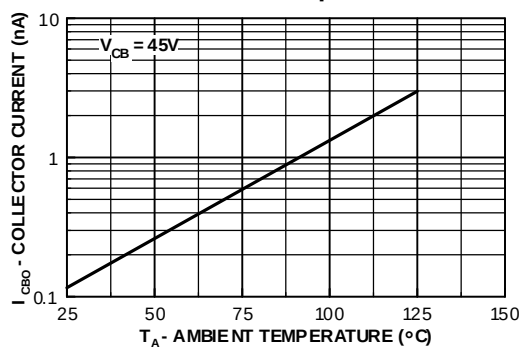
Base-Emitter Saturation Voltage vs Collector Current



Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

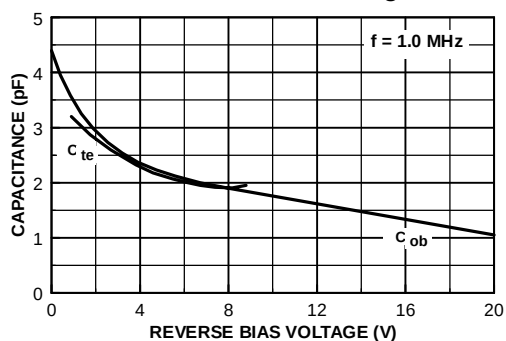


NPN General Purpose Amplifier

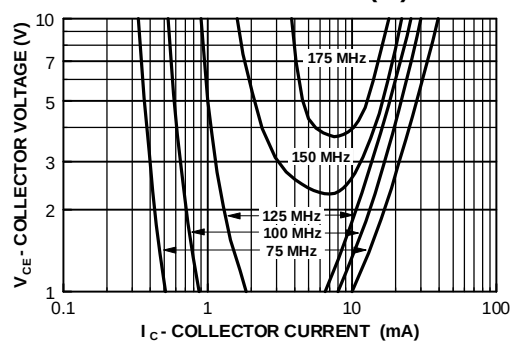
(continued)

Typical Characteristics (continued)

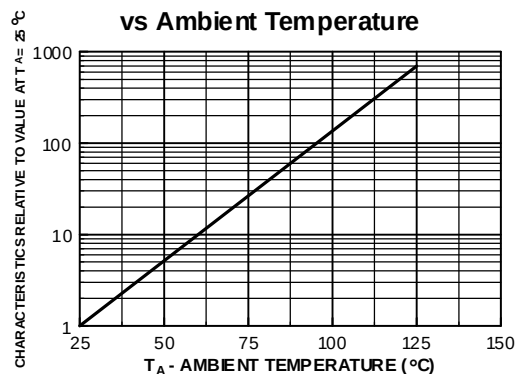
Input and Output Capacitance
vs Reverse Bias Voltage



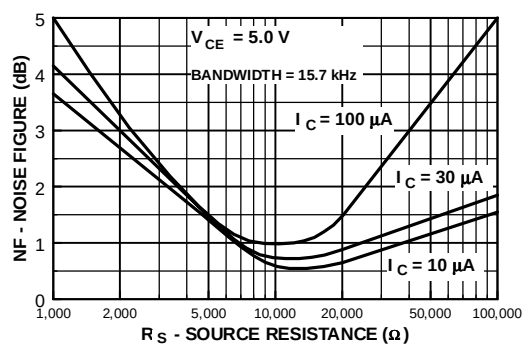
Contours of Constant Gain
Bandwidth Product (f_T)



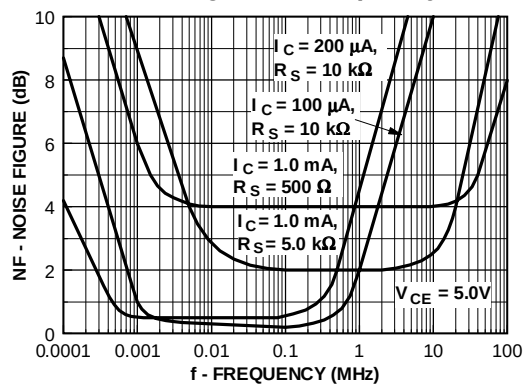
Normalized Collector-Cutoff Current
vs Ambient Temperature



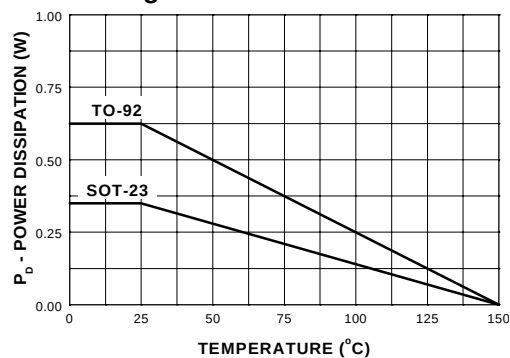
Wideband Noise Frequency
vs Source Resistance



Noise Figure vs Frequency



Base-Emitter Saturation
Voltage vs Collector Current

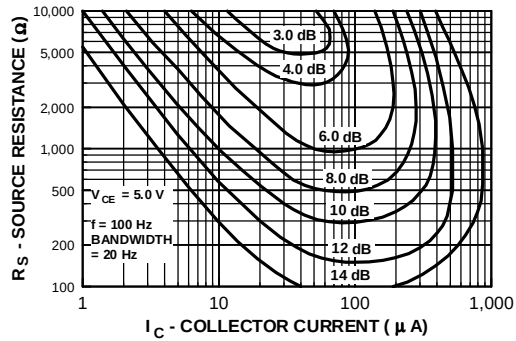


NPN General Purpose Amplifier (continued)

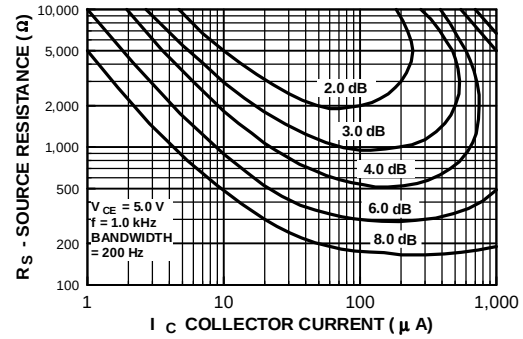
2N5210/MMBT5210

Typical Characteristics (continued)

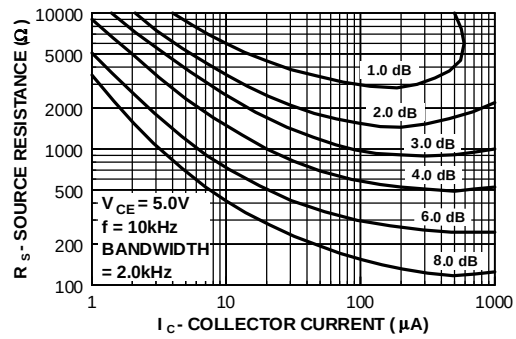
Contours of Constant
Narrow Band Noise Figure



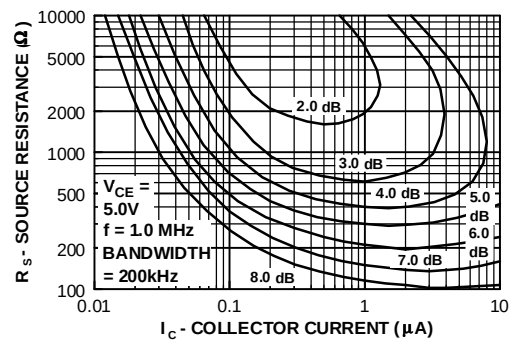
Contours of Constant
Narrow Band Noise Figure



Contours of Constant
Narrow Band Noise Figure



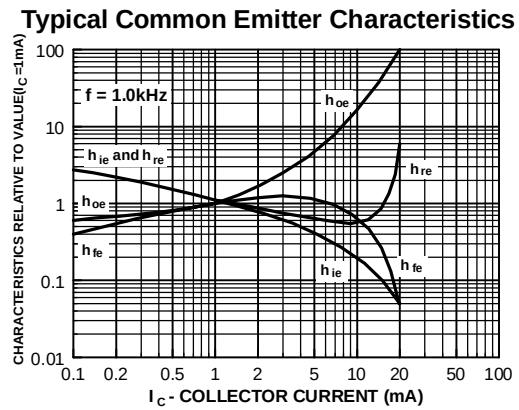
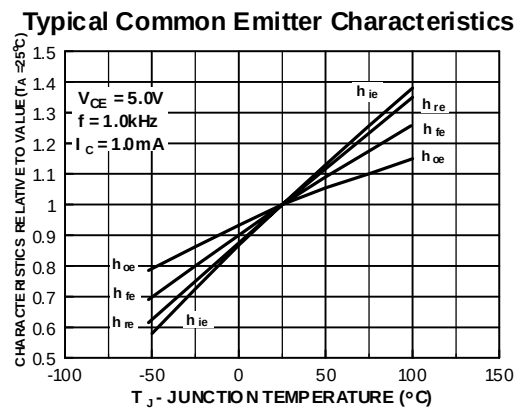
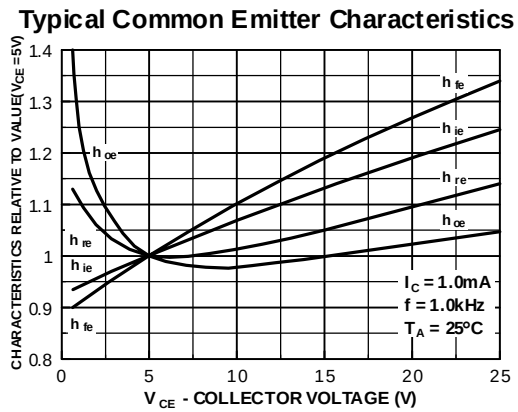
Contours of Constant
Narrow Band Noise Figure



NPN General Purpose Amplifier (continued)

2N5210/MMBT5210

Typical Common Emitter Characteristics (f = 1.0 kHz)



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} TM	FAST [®]	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST ^r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.